Electrical Transport in metallofullerene nanotube peapods

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Single-wall carbon nanotubes (SWNTs) have opened up a new possibility for novel components in miniaturized electronic devices. SWNTs are onedimensional structure that exhibit metallic or semiconducting behavior. Semiconducting nanotubes have been shown to function as field-effect active channels<sup>1</sup>, nanorectifiers<sup>2</sup>. Due to the doping effect of adsorbed oxygen molecules and the charge transfer with defined electrodes, pristine SWNTs show p-type semiconducting behavior. For complementary logic circuitry, various chemical modification achieved by doping semiconducting nanotubes have been demonstrated<sup>3,4</sup>. However, the stability of alkali-metal been doped nanotubes<sup>3,4</sup> is sensitive to the ambient environment. Therefore, ambient stable chemical doping by metallofullerene will be a good starting point for the band engineering of carbon-based nanoelectronics.

The mono-metallofullerene encapsulating single lanthanide element,  $Ln@C_{82}$  (Ln = Ce, Nd, Gd, Dy,...), has been confirmed by electron spin resonance and UV-Vis-NIR adsorption spectra to show charge transfer from the encaged atom to the C<sub>82</sub> cage,<sup>5</sup> resulting in the charge state of  $Ln^{3+}@C_{82}^{3-}$ . The insertion of metallofullerenes into the nanotube is therefore expected to lead to further charge transfer from the  $C_{82}$  cage to the tube and the electrical properties of the carbon nanotubes would be substantially modified.

The insertion of  $Dy@C_{82}$  into the inner hollow space of the SWNTs host was carried out by gas phase diffusion of  $Dy@C_{82.}^6$  The individual metallofullerene peapods were deposited on a degenerately doped silicon substrate with SiO<sub>2</sub> insulating layer on top and predefined electrodes. Fig. 1 shows the transport measurement in one single tube. At room temperature, the doped nanotube shows p-type behavior as seen from the response to a back gate. As the temperature decreases, the conductance becomes n-type. It reveals that the  $Dy@C_{82}$  molecules function as electron donors and transfer charge to the carbon nanotube host. The amount of charge transferred varies with temperature. At T < 215 K metallic behavior is observed, indicating the degenerate state by doping. Below about 75 K, single-electron charging phenomena dominate the transport and show irregular Coulomb blockade oscillation, implying that the insertion of  $Dy@C_{82}$  splits the tube into a series of several quantum dots.



Fig. 1 (a)-(c) Gate voltage dependence of conductance measured at  $V_{DS} = 4$  mV at various temperatures. The curves in (c) are displaced for clarity. The insets are schematic plots of the band diagram.

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